Electronic Supplementary Information

Chloroformamidine hydrochloride as a molecular linker towards efficient and stable perovskite solar cells

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Experimental Procedures

Materials

All chemicals used in this work are commercially available and were used without additional purification steps. The SnO₂ aqueous colloid (15.0 wt%) was obtained from Alfa Aesar (tin(IV) oxide). *N*,*N*-dimethylformamide (DMF) and dimethyl sulfoxide (DMSO) were purchased from Sigma-Aldrich. Isopropanol (IPA) was purchased from Aladdin. Lead iodide (PbI₂) (99.99%), formamidinium iodide (FAI) (99.5%), methylammonium bromide (MABr) (99.9%), methylammonium chloride (MACI) (99.5%) and 2,2',7,7'-tetrakis(*N*,*N*-di-*p*-methoxyphenylamine)-9,9'-spirobifluorene (Spiro-OMeTAD) (99.5%) were purchased from Advanced Election Technology CO., Ltd. Bis(trifluoromethane)sulfoninide lithium salt (Li-TFSI) was purchased from Sigma-Aldrich. FK209 (Co(III)TFSI) and 4-*tert*-Butylpyridine (*t*BP) were purchased from Xi'an Polymer Light Technology Corp, China. Chloroformamidine hydrochloride (CFA) (98.0%) was obtained from Aladdin.

Device fabrication

ITO substrates were cleaned by sequentially washing with ethanol, IPA and ethanol in ultrasonic bath for 30 min each, then dried by flowing nitrogen and treated with UV-ozone for 30 min before use. The SnO₂ aqueous colloidal (15.0 wt%) was diluted using deionized water to the concentration of 3.0 wt%. Then CFA (0.2–1.0 mg mL⁻¹) was added into the SnO₂ aqueous colloidal (3.0 wt%) to obtained CFA@SnO₂ precursor solutions. These solutions were stirred at room temperature for 30 minutes. The SnO₂ and CFA@SnO₂ layers were fabricated by spin-coating SnO₂ or CFA@SnO₂ precursor solutions on ITO substrates at 4000 r.p.m. for 30 s, and then annealed for 30 min at 150 °C in ambient air. Once cooled to room temperature, the samples were treated with UV-ozone for 25 min before making perovskite films.

The FAPbI₃-based perovskite films were deposited on different ETLs using twostep spin coating method.¹ First, the precursor PbI₂ (691.5 mg, 1.5 mol L⁻¹) dissolved in DMF/DMSO (v/v 9/1) solution was spin-coated onto the SnO₂ or CFA@SnO₂ substrates at 1500 r.p.m. for 30 s, and then annealed at 70 °C for 1 min. Second, after the PbI₂ film cooled down to room temperature, 50 μ L of the organic mixture solution of FAI: MABr: MACI (60 mg : 6 mg : 9 mg in 1 mL IPA) was spin-coated onto the PbI₂ film at 1700 r.p.m for 30 s. When the resulting films turned from orange to dark brown in glove box, they were taken out from the glove box and thermally annealed at 150 °C for 15 min in ambient air (30%–40% humidity). It has reported that humidity is beneficial in obtaining high-quality perovskite films.² Then films were transferred into a N₂-filled glovebox.

Then, the Spiro-OMeTAD solution, which consisted of 72.3 mg Spiro-OMeTAD, 17.5 μ L Li-TFSI stock solution (520 mg Li-TFSI in 1 ml acetonitrile), 29 μ L FK209 stock solution (300 mg FK209 in 1 ml acetonitrile), 29 μ L *t*BP and 1 mL chlorobenzene, was spin-coated on top of the perovskite layer at 3000 r.p.m for 30 s as the hole transport layer. These samples were retained in a desiccator overnight. Finally, 100 nm Au film was deposited via thermal evaporation as a counter electrode. The device area of 0.04 cm² and 0.10 cm² were determined by a metal mask.

Characterization

Photocurrent density–voltage (J-V) curves were measured using a solar simulator (SS-F5-3A, Enlitech) along with AM 1.5G spectra whose intensity was calibrated by certified standard silicon solar cell (SRC-2020, Enlitech) at 100 mW cm⁻², and a Keithley 2400 source meter. J-V curves were measured from -0.1 V to 1.2 V (forward scan, FS) or from 1.2 V to -0.1 V (reverse scan, RS) with a scan rate of 20 mV s⁻¹.

X-ray diffraction (XRD) patterns were acquired with a Rigaku SmartLab diffractometer using Cu Kα radiation provided applied current and voltage values of 200 mA and 40 kV, respectively. The scan rate of 20 °/min was applied to record the XRD patterns in the range of 5–60° (2 theta). Scanning electron microscopy (SEM) was performed on a JSM-7800F microscope (JEOL) with an accelerating voltage of 3 kV. UV-visible (UV-vis) absorption spectra were recorded on a UV-vis spectrophotometer (JASCO V-650). The Attenuated total reflectance-Fourier transform infrared (ATR-FTIR) spectra were recorded with a Nicolet iS50 infrared Fourier transform microscope by Thermo-Fisher Scientific. A Fluorescence spectrophotometer (QM400, PTI) with an excitation wavelength of 520 nm was used to collect steady-state photoluminescence (PL) spectra. The time-resolved PL (TRPL)

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spectra were recorded on a FLS920 fluorescence spectrometer (Edinburgh Instruments) in air at room temperature. A picosecond pulsed diode laser (406.8 nm) was used as the excitation source.

X-ray photoelectron spectroscopy (XPS) measurements were performed on a Thermo-Fisher ESCALAB 250Xi system with a monochromatized AI K α under the pressure of 4.0 × 10⁻⁹ mbar and all the binding energies were calibrated by C 1s (284.8 eV) as a reference. Ultraviolet photoelectron spectroscopy (UPS) was performed on a photoelectron spectrometer (Thermo-Fisher ESCALAB XI+). The contact angle was measured using a DSA100 optical contact-measuring system (KRUSS).

Electron mobility of SnO₂ and CFA@SnO₂ film

The space charge-limited current (SCLC) method³ was employed to measure the electron mobility of SnO₂ film and CFA@SnO₂ film. Specifically, the electron-only device was designed and fabricated using ITO/ETL/Au structure, as shown in the inset in Fig. 1e. The dark J-V curves of the devices were performed on a Keithley 2400 source meter. The electron mobility (μ_e) is extracted by fitting the J-V curves using the Mott-Gurney law (1):

$$\mu_e = \frac{8JL^3}{9\varepsilon_0 \varepsilon_r (V_{app} - V_r - V_{bi})^2} \tag{1}$$

where μ_e is the electron mobility, J is the current density, L is the thickness of SnO₂ film, ϵ_0 is the vacuum permittivity, ϵ_r is the relative dielectric permittivity of SnO₂ (ϵ_r = 9.9), V_{app} is the applied voltage, V_r is the voltage loss due to constant resistance and series resistance across the electrodes, and V_{bi} is the built-in voltage owing to the different work function between the anode and cathode.



Fig. S1. Photographs of the SnO₂ (3.0 wt%) colloidal solution with different CFA amounts (0, 0.4, 1.0, 1.5 mg mL⁻¹, respectively).

The surface of SnO₂ nanoparticles is negatively charged in colloid solution. In addition, KOH is added as a stabilizer in commercial SnO₂ colloid solution to well-disperse the ultra-small nanoparticles.^{4, 5} We investigated the effect of CFA concentration with the acidic property on SnO₂ colloid solution. As the result, the mixed solution remains clear and transparent after introducing 0.4 mg mL⁻¹ and 1.0 mg mL⁻¹ CFA, but it becomes milky white jelly by introducing 1.5 mg mL⁻¹ CFA.



Fig. S2. (a) Transmittance spectra. (b) UV-vis absorption spectra. (c) Tauc plot derived from UV-vis absorption spectra of SnO_2 and $CFA@SnO_2$ films deposited on glass, respectively.



Fig. S3. XRD patterns of SnO₂ and CFA@SnO₂ films, respectively.



Fig. S4. XPS spectra of SnO_2 and $CFA@SnO_2$ films, respectively.



Fig. S5. XPS spectra of the Cl 2p orbital of SnO₂ and CFA@SnO₂ films, respectively.



Fig. S6. (a) UPS spectra. (b) The electron cut off region and (c) the valence band region of the UPS spectra for SnO_2 and $CFA@SnO_2$ films, respectively.



Fig. S7. Schematic diagram of the manufacturing process for SnO₂ films and perovskite films.



Fig. S8. Water contact angles measured on SnO₂ and CFA@ SnO₂ films, respectively.



Fig. S9. XRD patterns of Pbl_2 films deposited on SnO_2 and $CFA@SnO_2$ substrates, respectively.



Fig. S10. (a) UV-vis absorption spectra. (b) The enlarged part of the dotted box part in Figure (a).



Fig. S11. ATR-FTIR spectra in the range of (a) 1800-1000 cm⁻¹ and (b) 800-400 cm⁻¹ of PbI₂, CFA, CFA-PbI₂ samples.

The C=N stretching vibration peak of pristine CFA is at 1687 cm⁻¹, which is reduced to 1674 cm⁻¹ in the CFA-Pbl₂ sample.⁶ The peak assigned to -NH₃⁺ bend vibration appears at 1454 cm⁻¹ of pristine CFA, and is shifted toward decreased wavenumbers in the CFA-Pbl₂ sample (1450 cm⁻¹).⁶ Moreover, the C-Cl stretching vibration peak at 645 cm⁻¹ of pristine CFA is reduced to 642 cm⁻¹ in the CFA-Pbl₂ sample.⁷ The peak shift demonstrates the chemical interaction between Pbl₂ and CFA.



Fig. S12. J-V curves of electron-only devices under dark with SnO₂ and CFA@SnO₂ ETL, respectively. The inset displays the structure of the electron-only devices.

When a voltage is applied to the ITO electrode, electrons are injected to ETL from the perovskite layer. The J-V curve reveals that the CFA@SnO₂-based device exhibits higher current density than the SnO₂-based device at the same voltage, which indicates that the electron injection becomes easier from the perovskite layer to the CFA@SnO₂ ETL than to the SnO₂ ETL⁸.



Fig. S13. J_{SC} versus light intensity plots of PSCs based on SnO₂ and CFA@SnO₂ ETLs.



Fig. S14. (a) J-V curves and (b) PCE variation of PSCs with different amounts of CFA in SnO₂ ETLs. (0, 0.2, 0.4, 0.6 mg mL⁻¹).



Fig. S15. J-V curves of champion devices based on SnO_2 and $CFA@SnO_2$ ETLs under reverse scan.



Fig. S16. Statistical distribution of the (a) V_{OC} , (b) J_{SC} , (c) FF and (d) PCE of SnO₂-based and CFA@SnO₂-based PSCs, respectively. The error bars were obtained from 20 measured samples for each condition (active area: 0.04 cm²).



Fig. S17. Statistical distribution of the (a) V_{OC} , (b) J_{SC} , (c) FF and (d) PCE of SnO₂-based and CFA@SnO₂-based PSCs, respectively. The error bars were obtained from 20 measured samples for each condition (active area: 0.10 cm²).



Fig. S18. Steady-state current density and PCE measured at a maximum power point of 0.94 V for the device based on SnO_2 ETL under AM 1.5G illumination (active area: 0.04 cm²).

Table S1. Calculated relative amounts of lattice oxygen (O_L) and vacancy oxygen (O_V) for the SnO₂ and CFA@SnO₂ film by fitting peak area.

Films	O _L (eV)	O _L (%)	O _V (eV)	O _V (%)
SnO ₂	530.47	64.5	531.61	35.5
CFA@SnO ₂	530.44	72.5	531.66	27.5

Table S2. Calculated valence band maximum (E_{VBM}) and conduction band minimum (E_{CBM}) from $E_{cut-off}$, E_{onset} and E_g for the SnO₂ and CFA@SnO₂ film.

Films	E _{cut-off} (eV)	E _F (eV)	E _{onset} (eV)	E _{∨BM} (eV)	E _g (eV)	E _{CBM} (eV)
SnO ₂	16.26	-4.96	2.65	-7.61	4.24	-3.37
CFA@SnO ₂	16.41	-4.81	3.77	-8.58	4.25	-4.33

Table S3. Parameters of the TRPL spectra of perovskite films deposited on SnO_2 and CFA@SnO₂ substrates, respectively.

Films	$ au_1$ (ns)	A ₁ (%)	$ au_2$ (ns)	A ₂ (%)	$ au_{ave}$ (ns)
ITO / SnO ₂ / PVK	134.83	16.55	590.31	83.45	570.57
ITO / CFA@SnO ₂ / PVK	119.19	24.87	469.66	75.13	442.50

ETL	V _{oc} (V)	J _{SC} (mA cm ⁻²)	FF (%)	PCE (%)
SnO ₂	1.15	24.22	74.31	20.70
CFA-0.2@SnO ₂	1.16	24.44	74.39	21.09
CFA-0.4@SnO ₂	1.17	24.54	76.55	21.98
CFA-0.6@SnO ₂	1.17	24.46	74.91	21.44

Table S4. Photovoltaic parameters of devices with different amounts of CFA in SnO_2 ETLs (active area: 0.1 cm²).

Table S5. Photovoltaic parameters of champion devices based on SnO₂ and CFA@SnO₂ ETL.

Active area (cm ²)	Devices	V _{oc} (V)	J _{SC} (mA cm ⁻²)	FF (%)	PCE (%)
0.04	Control	1.14	25.77	76.26	22.40 (21.57 ± 0.83) ^a
	CFA	1.17	25.79	77.77	23.47 (22.69 ± 0.78)
0.10	Control	1.14	24.31	77.23	21.40 (20.84 ± 0.56)
	CFA	1.16	25.01	77.71	22.54 (21.90 ± 0.64)

^a The average PCE obtained from 20 devices and the standard error.

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